

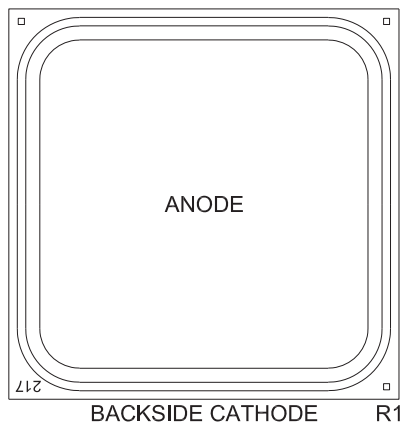
PROCESS CPD34X
Schottky Rectifier
10 Amp Schottky Rectifier Chip



PROCESS DETAILS

Die Size	85 x 85 MILS
Die Thickness	5.9 MILS ± 0.8 MILS
Anode Bonding Pad Area	78 x 78 MILS
Top Side Metalization	Al – 30,000Å
Back Side Metalization	Ti/Ni/Au - 1,600Å/5,550Å/1,500Å

GEOMETRY



GROSS DIE PER 5 INCH WAFER

2,260

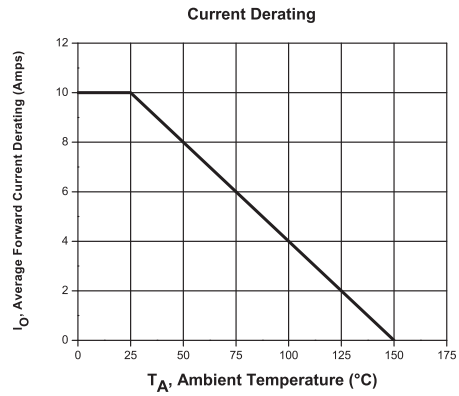
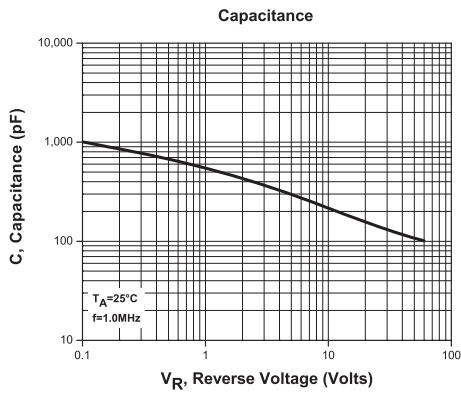
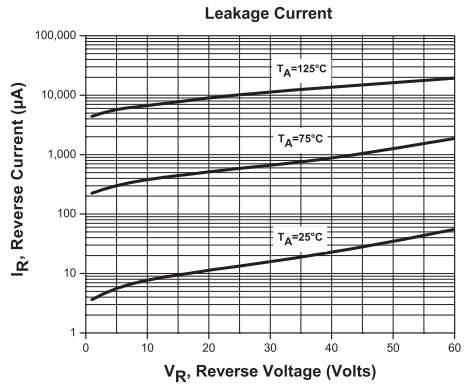
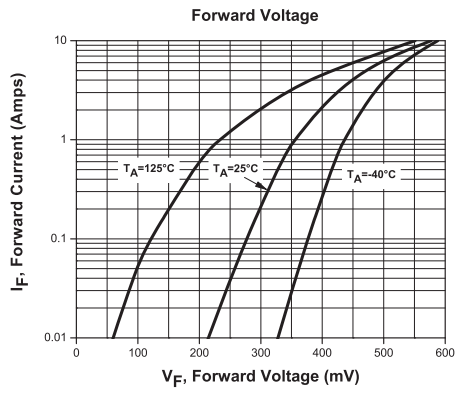
PRINCIPAL DEVICE TYPE

CSHD10-60

R0 (17-October 2011)

PROCESS CPD34X

Typical Electrical Characteristics



R0 (17-October 2011)